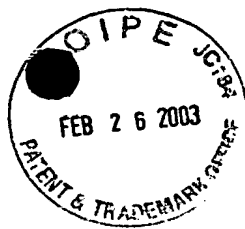


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#10B
Amdt
Darius
3/3/03

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

Masahiro TANAKA

: GROUP ART UNIT: 2815

SERIAL NO.: 09/853,661✓

:

FILED: May 14, 2001✓

: EXAMINER: Jose R. DIAZ

FOR: ELECTRODE CONTACT SECTION
OF SEMICONDUCTOR DEVICE

RECEIVED
FEB 28 2003
TECHNOLOGY CENTER 2800

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office Action dated November 26, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION

Please amend the paragraph beginning at page 1, line 12, as shown in the marked-up copy, to read as follows:

B1
In the prior art, an electrode section incorporated in a semiconductor device is formed of an impurity layer provided in a semiconductor layer, and an electrode (made of, for example, a metal such as aluminum) that is in contact with the impurity layer. The impurity layer is often formed by ion implantation for the purpose of low cost.